

ZAHRAA JAMEEL ABDULKAREEM. SOME PROPERTIES OF TiO₂ NANOPARTICLES ON POROUS SILICON FOR OPTOELECTRONICS APPLICATION. UNIVERSITY OF TECHNOLOGY / Department of Laser and Optoelectronics Engineering. M.Sc. Supervisor : Dr. KADHIM A. HUBEATIR and Dr. UDAY M. NAYEF.2015.110 p.

Abstract

In this thesis, the research is divided into three sections. The first section includes the preparation of TiO₂ NPs by pulsed laser ablation in liquid (PLAL) technique. The Nd:YAG laser with different wavelengths (532 and 1064 nm) and energies (200, 400 and 600 mJ/pulse) was used to irradiate titanium target at 450 pulses. The second section includes the formation of Porous Silicon (PS) with Photoelectrochemical etching (PECE) method at different etching current densities (10, 30 and 50 mA/cm²) and 20% Hydrofluoric (HF) acid concentration for 10 minutes. In the last section, the optimum results of TiO₂ NPs were used on the best result of PS.

The results of TiO₂ NPs refer to its n-type semiconductor with crystallites size decreases from 72.07 to 57.76 nm accompanied with decreasing in TiO₂ NPs concentration and increasing band gap energy (3.95-4.02 eV) when laser wavelength reduced. Also, the results of PS show the nanostructure (mesoporous silicon) formed, with increasing pore diameter from 14.18 to 22.12 nm with increasing etching current density.

The morphological properties of TiO₂ NPs deposited on PS presented a good adhesion between these nanostructures leading to improve the structural stability of the PS substrate. The reflectivity gives a clear observation about enhancement of PS antireflection properties after coated with TiO₂ NPs. The electrical resistivity of the PS layer increased with the pore diameter and became higher after deposition of TiO₂ NPs. The capacitance-voltage results show that built-in potential increased with TiO₂ NPs concentration. So the detector measurements of TiO₂ NPs/PS exhibited a higher responsivity (0.053 A/W) and quantum efficiency (20.25%) with higher TiO₂ NPs concentration.

Keywords: TiO₂ nanoparticles, Porous silicon, Photodetector.